

MA2Z392

N type GaAs epitaxial planar type

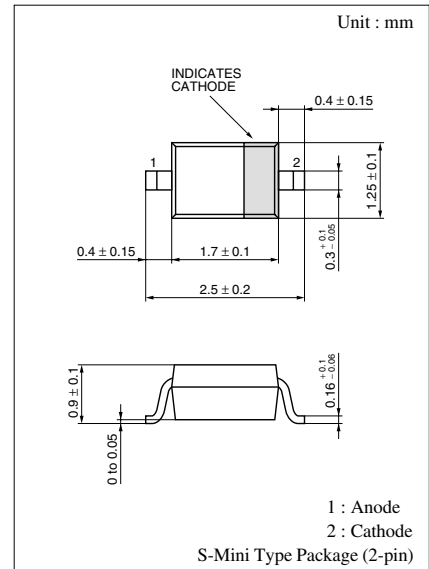
For VCO of a communications equipment

■ Features

- Small series resistance r_D and high Q value
- Large capacitance ratio during low-voltage operation

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	10	V
Forward current (DC)	I_F	40	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$



Marking Symbol: 7N

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 6\text{ V}$			50	nA
Forward voltage (DC)	V_F	$I_F = 400\text{ mA}$			0.8	V
Reverse voltage (DC)	V_R	$I_R = 1\ \mu\text{A}$	10			V
Diode capacitance	$C_{D(1V)}$	$V_R = 1\text{ V}, f = 1\text{ MHz}$	3.5	5.0	6.5	pF
	$C_{D(4V)}$	$V_R = 4\text{ V}, f = 1\text{ MHz}$	1.0	1.8	2.6	pF
Series resistance*	r_D	$C_D = 2.3\text{ pF}, f = 470\text{ MHz}$		0.3	0.4	Ω

Note) 1. Rated input/output frequency: 470 MHz

2. *: r_f measuring instrument: RF IMPEDANCE ANALYZER

